Amendment to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-18 (Canceled)

Claim 19. (New) A method for manufacturing a high electron mobility transistor, comprising:

forming an electron accumulation layer on a substrate;

forming an isolated element region on the electron accumulation layer, the isolated element region having an electron supply layer;

forming a source electrode and a drain electrode on the electron supply layer of the isolated element region, being spaced for each other; and

forming a hole absorption electrode on the electron accumulation layer, the hole absorption electrode being spaced from the electron supply layer and simultaneously forming a gate electrode on the electron supply layer of the isolated element region.

Claim 20. (New) The method of claim 19, wherein

the forming of the isolated element region includes selectively removing the electron supply layer to isolate the element region.

Claim 21. (New) The method of claim 20, wherein

the forming of the hole absorption electrode includes selectively removing the electron supply layer.

Claim 22. (New) The method of claim 21, wherein

the forming of the hole absorption electrode includes forming the hole absorption electrode on the electron accumulation layer via a semiconductor layer having a smaller bandgap width than that of the electron accumulation layer.

Claim 23. (New) The method of claim 21, wherein

the forming of the hole absorption electrode includes forming the hole absorption electrode on the electron accumulation layer via a p-type semiconductor layer.

Claim 24. (New) The method of claim 21, wherein

the forming of the hole absorption electrode includes forming the hole absorption electrode adjacent to the source electrode.

Claim 25. (New) The method of claim 21, wherein

the forming of the hole absorption electrode includes forming the hole absorption electrode in parallel with the gate electrode in a gate width direction having the substantially the same length as that of the source electrode in the gate width direction.